

DESCRIPTION

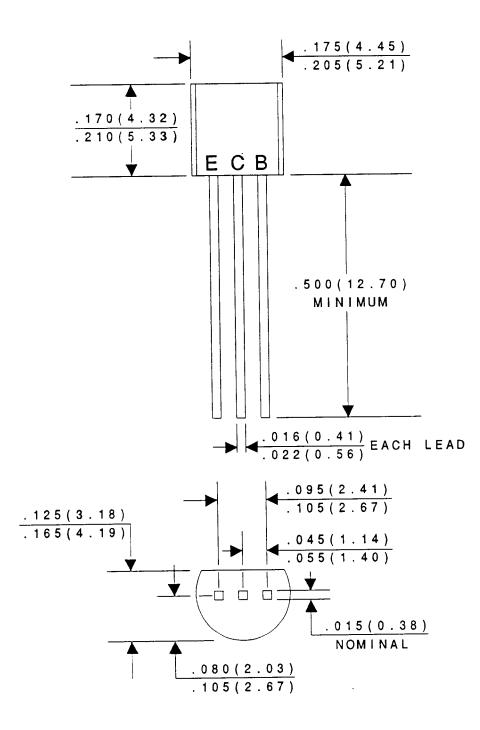
The CENTRAL SEMICONDUCTOR 2N5366, 2N5367 types are PNP Silicon Planar Epitaxial Transistors designed for general purpose switching and amplifier applications.

<u>MAXIMUM RATINGS</u> $(T_A = 25^{\circ}C)$

SYMBOL		UNITS
VCBO	40	v
V _{CEO}	40	V
V _{EBO}	4.0	V
I _C	300	mA
I _C	700	mA
PD	625	mW
T _J ,T _{stg}	-65 to +150	°C
θ _{JA}	0.2	^o C/mW
	V _{CBO} V _{CEO} V _{EBO} I _C I _C P _D T _J ,T _{stg}	VCBO 40 VCEO 40 VEBO 4.0 IC 300 IC 700 PD 625 TJ, Tstg -65 to + 150

<u>ELECTRICAL CHARACTERISTICS</u> ($T_A = 25^{\circ}C$ unless otherwise noted)

		<u>2N5</u>	<u>2N5366</u> <u>2N5367</u>			
<u>SYMBOL</u>	TEST CONDITIONS	MIN	<u>MAX</u>	<u>MIN</u>	<u>MAX</u>	<u>UNITS</u>
Сво	V _{CB} =40V		100		100	nA
I _{CBO}	V _{CB} =40V, T _A =100 ^o C		10		10	μΑ
ICES	V _{CB} =40V		100		100	nA
I _{EBO}	$V_{EB} = 4.0V$		10		10	μA
BVCEO	I _C = 10mA	40		40		V
VCE(SAT)	$I_{C} = 50 \text{mA}, I_{B} = 2.5 \text{mA}$		0.25		0.25	V
V _{CE} (SAT)	I _C =300mA, I _B =30mA		1.0		1.0	V
VBE(SAT)	$I_{C} = 50 \text{mA}, I_{B} = 2.5 \text{mA}$,	1.1		1.1	V
VBE(SAT)	I _C =300mA, I _B =30mA		2.0		2.0	V
VBE(ON)	$V_{CE} = 10V, I_{C} = 2.0mA$	0.5	0.8	0.5	0.8	V
hFE	$V_{CE} = 10V, I_{C} = 2.0mA$	80		200		
h _{FE}	V _{CE} = 1.0V, I _C = 50mA	100	300	250	500	
h _{FE}	V _{CE} =5.0V, I _C =300mA	40		. 75		
С _{оb}	$V_{CB} = 10V, I_E = 0, f = 1.0MHz$		8.0		8.0	рF
C _{ib}	$V_{EB} = 0.5V$, $I_{C} = 0$, $f = 1.0MHz$		35		35	рF
h _{fe}	$V_{CE} = 10V, I_{C} = 2.0 \text{mA}, f = 1.0 \text{kHz}$	80	450	200	750	
fT	$V_{CE} = 10V, I_{C} = 2.0mA$	250) ΤΥΡ	250	TYP	MHz



All Dimensions in Inches (mm).



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- PbSn plating options
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- Application notes
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- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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